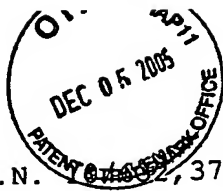


U.S.S.N. 10/632,379



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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: Yang et al.                      Group Art Unit: 2829  
Serial No.: 10/632,379                      Examiner: D. Farahani  
Filed: 08/01/2003                      In Response to Office Action  
Dated: 08/30/2005

For:              FIELD EFFECT TRANSISTOR (FET) DEVICE HAVING  
CORRUGATED STRUCTURE AND METHOD FOR FABRICATION THEREOF

Attorney Docket No.: 67,200-377

**CERTIFICATE OF MAILING OR FACSIMILE TRANSMISSION**

I hereby certified that this correspondence is (1) ☒ being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to the Commissioner for Patents, P O Box 1450, Alexandria, VA 22313-1450 on November 30, 2005; or (2) ☐ being facsimile transmitted to the United States Patent and Trademark Office at facsimile number (571)-273-8300 November \_\_, 2005.

Randy W. Tung

Printed Name

Please forward all correspondence to  
TUNG & ASSOCIATES  
838 W. Long Lake Road, Suite 120  
Bloomfield Hills, MI 48302

  
Signature

11/30/05

Date

**Request For Reconsideration**

Assistant Commissioner  
for Patents  
P.O. Box 1450  
Alexandria, Va 22313-1450

Dear Sir:

In response to an Office Action mailed 08/30/2005,  
please enter the following amendments and consider the following  
remarks.